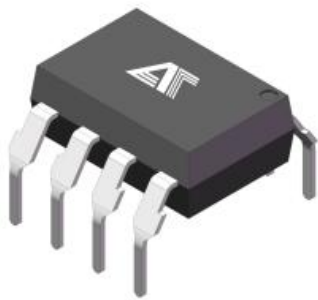




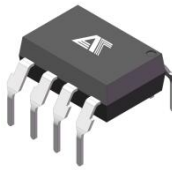
栅极驱动光耦
Gate driven optocoupler

EL3150S

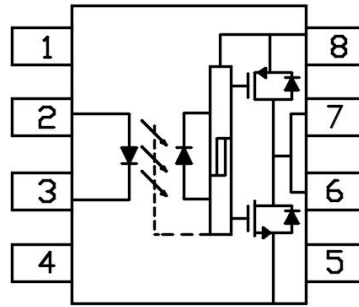
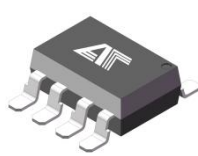
Product Data Sheet

AOTE DCC
RELEASE

DIP8-M



SMD8



Pin Configuration

- 1.4.NC
- 2.Anode
- 3.Cathode
- 5.VEE
- 6.VO2
- 7.VO1
- 8.VCC

◆ 封装逻辑原理图 Encapsulation logic schematic

EL3150S 光耦采用高效光电转换技术，结合先进封装工艺，提供输入输出间的可靠隔离，支持DIP8-M、SMD8两种封装形式，适配多样化场景需求。

The EL3150S optocoupler adopts high-efficiency photoelectric conversion technology and advanced packaging processes, providing reliable input-output isolation. It supports Two package types (DIP8-M, SMD8) to meet diverse application requirements.

◆ 产品特征Product features

- 输入-输出隔离电压 $V_{ios}=5000V_{rms}$
Input output isolation voltage: $V_{ios}=5000V_{rms}$
- 15 kV/ μs 最小共模抑制;15 kV/ μs minimum Common Mode Rejection
- 10V 至 30V 宽工作电压范围; 10V ~ 30V Wide operating VCC Range
- 最大峰值输出电流0.6A ; Maximum peak output current 0.6A
- 爬电距离>7.0mm ; Creepage distance > 7.0mm;
- 输入-输出绝缘距离 >0.4mm ; Input-Output insulation Thickness > 0.4mm
- 防潮等级 class1; MSL class1
- 产品符合 ROHS、REACH 及 HF 等环保法规要求;
The products comply with ROHS, REACH and HF;

◆ 应用领域 Applications

- 工业自动化和电子电力: Industrial automation and electronic power; 用于变频器、伺服驱动器等设备的栅极隔离驱动; Gate isolation drive for devices such as frequency converters and servo drives;
- 新能源与电力系统: New Energy and Power Systems车载充电桩(OBC)、电机控制器驱动功率器件; Vehicle mounted charging station (OBC), motor controller drives power devices;
- 电力控制与保护装置: Power control and protection device 固态继电器(SSR)、断路器驱动电路中隔离控制端与功率端; Solid state relay (SSR), isolation control terminal and power terminal in circuit breaker drive circuit
- 噪声环境设备和精密医疗仪器: Noise environment equipment and precision medical instruments适用于电磁干扰严重的工业场景 (如电焊机、电磁炉) ; Suitable for industrial scenarios with severe electromagnetic interference, such as welding machines and induction cookers



◆ 极限参数 Absolute Maximum Ratings (Ta =25°C)

参数 Parameter		符号 Symbol	额定值 Rating	单位 Unit
输入 Input	平均输入电流 Average Input Current	IF(AVG)	25	mA
	峰值瞬态输入电流 (<1μs pulse, 300pps) Peak Transient Input Current	IF(TRAN)	1	A
	输入反向电压 Reverse Input Voltage	VR	5	V
输出 Output	高电平峰值输出电流 “High” Peak Output Current	IOH(PEAK)	-0.6	A
	低电平峰值输出电流 “Low” Peak Output Current	IOL(PEAK)	0.6	A
	电源电压 Supply Voltage	VCC-VEE	0~35	V
	输出电压 Output Voltage	VO(PEAK)	0 ~VCC	V
隔离电压 Isolation Voltage		VISO	5000	Vrms
总功耗 Total Power Consumption		Ptot	200	mW
工作温度 Operating Temperature		Topr	-40 ~+110	°C
存储温度 Storage Temperature		Tstg	-55 ~+125	°C
焊接温度 Soldering Temperature		Tsol	260	°C

◆ 推荐操作条件 Recommended Operating Conditions

参数 Parameter	符号 Symbol	最小值 Min	最大值 Max.	单位 Unit
电源电压 Supply Voltage	VCC-VEE	10	30	V
输入电流(ON) Input Current(ON)	IF(ON)	7	16	mA
输入电压(OFF) Input Voltage(OFF)	VF(OFF)	0	0.8	V

◆ 产品特性参数Product characteristic parameters (Ta =25°C)

参数 Parameter		符号 Symbol	条件 Condition	最小 Min.	典型 Typ.	最大 Max.	单位 Unit
输入端 Input	正向电压 Forward Voltage	VF	IF =10mA	1.2	1.5	1.8	V
	反向电流 Reverse Current	IR	VR =5V	-	-	10	μA
	输入开启电流 Input Turn On Current	IFLH	Io =0mA, VO >5V	-	2.2	5.0	mA
	输入关闭电压 Input Turn Off Voltage	VFHL	Io =0mA, VO <5V	0.8	-	-	V
	低电压锁定阈值 UVLO Threshold	VUVLO+	VO >5V	6.9	7.8	8.7	V
		VUVLO-	IF =10mA	5.9	6.7	7.5	V
	低电压锁定阈值迟滞 UVLO Hysteresis	UVLOHYS	-	-	1.6	-	V
输出端 Output	高电平输出电流 High Level Output Current	IOH	VO =VCC-4V	-	-0.4	-0.1	A
			VO =VCC-15V	-	-	-0.5	
	低电平输出电流 Low Level Output Current	IOL	VO =VEE+2.5V	0.1	0.6	-	A
			VO =VEE+12V	0.5	-	-	
	高电平输出电压 High Level Output Voltage	VOH	Io =-100mA	VDD-6	VDD-4	-	V
	低电平输出电压 Low Level Output Voltage	VOL	Io =100mA	VDD-0.6	VDD-0.35	-	V
	高电平电源电流 High Level Power Supply Current	ICCH	Vo=Open, IF =7 to 16mA	-	2.5	5	mA
	低电平电源电流 Low Level Power Supply Current	ICCL	Vo=Open, VF =-3 to 0.8V	-	2.7	5	mA

参数 Parameter		符号 Symbol	条件 Condition	最小 Min.	典型 Typ.	最大 Max.	单位 Unit
传输特性 Transfer Characteristics	隔离电阻 Isolation Resistance	RISO	VI-O ≤500V	-	10 ¹¹	-	Ω
	隔离电容 Isolation Capacitance	CISO	VI-O =0V, Freq=1.0MHz	-	1	-	pF
	低电平传输延迟 Propagation Delay Time to Low Output Level	TPHL	IF =7mA to 16mA Rg =47Ω , Cg =3nF, f=10kHz, 占空比=50%	100	300	500	ns
	高电平传输延迟 Propagation Delay Time to High Output Level	TPLH		100	300	500	ns
	脉冲失真 Pulse Width Distortion	PWD		-	-	300	ns
	传播延迟差 Propagation Delay Difference Between Any Two Parts	PDD		-350	-	350	ns
	输出上升时间(10% ~90%) Output Rise Time (10% ~90%)	TR	IF =7mA to 16mA, Rg =10Ω , Cg=10nF, F =10kHz, 占空比=50%	-	100	-	ns
	输出下降时间(90% ~10%) Output Drop Time (90% ~10%)	TF		-	100	-	ns
	UVLO 开启延迟 UVLO Turn On Delay	TUVLO ON	IF =10mA, VO >5V	-	0.8	-	μs
	UVLO 关闭延迟 UVLO Turn Off Delay	TUVLO OFF	IF =10mA, VO <5V	-	0.6	-	μs
	输出高电平共模抑制 Output High Level Common Mode Transient Immunity	CMH	TA =25°C VDD =30V VCM =1500V IF =10 ~ 16mA	15	30	-	kV/μs
	输出低电平共模抑制 Output Low Level Common Mode Transient Immunity	CML		15	30	-	kV/μs

◆ 电性特性曲线Electrical characteristic curve($T_a = 25^\circ\text{C}$)

Fig.2 High Level Output Current vs Ambient temperature

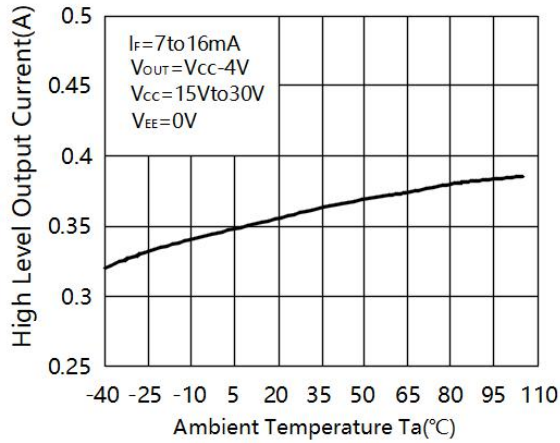


Fig.1 High Level Output Voltage vs Ambient Temperature

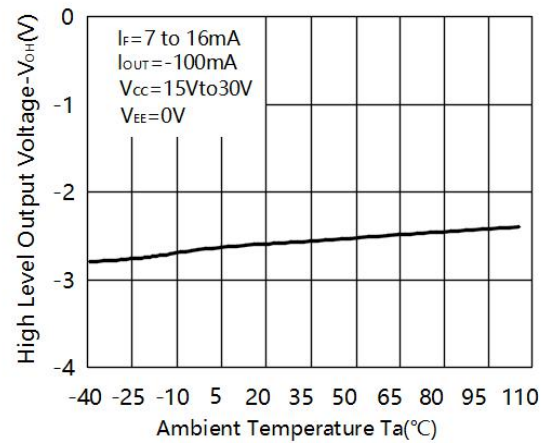


Fig.3 Low Level Output Voltage vs Ambient Temperature

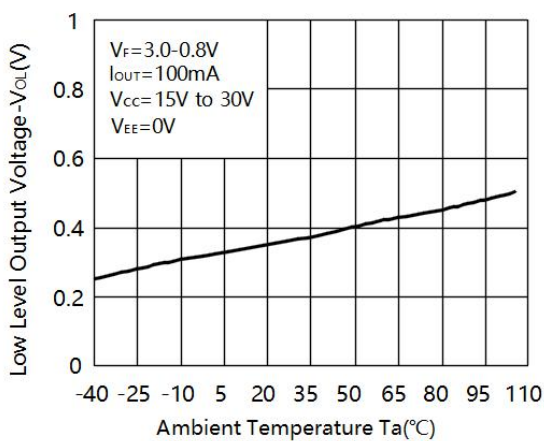


Fig.4 Supply Current vs Ambient temperature

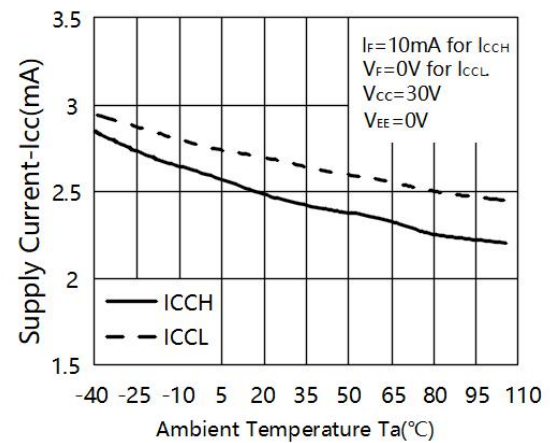


Fig.5 Supply Current vs Supply Voltage

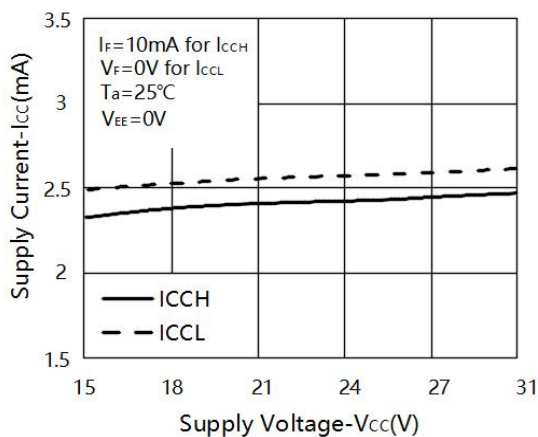


Fig.6 Output Voltage vs Threshold Input Current Low to Higt

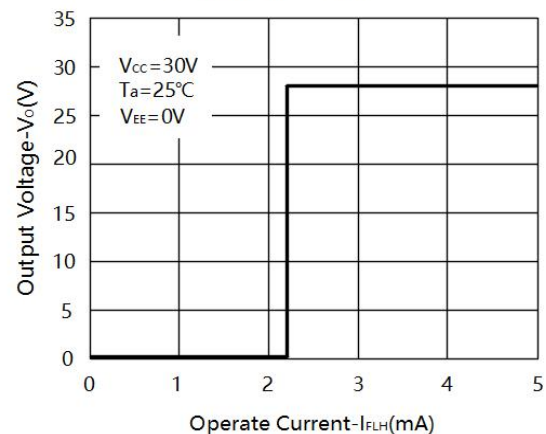


Fig.7 Threshold Input Current Low to High vs Ambient Temperature

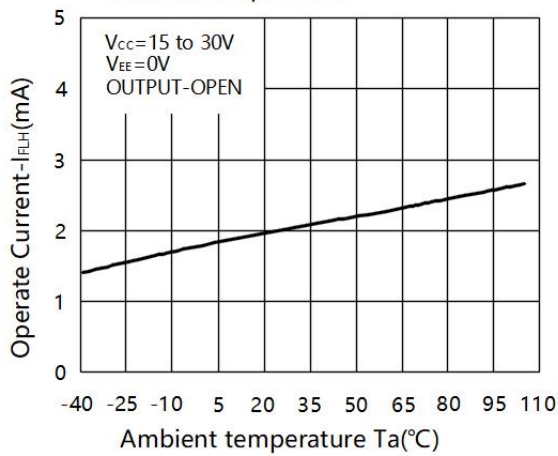


Fig.8 Propagation Delay vs Supply Voltage

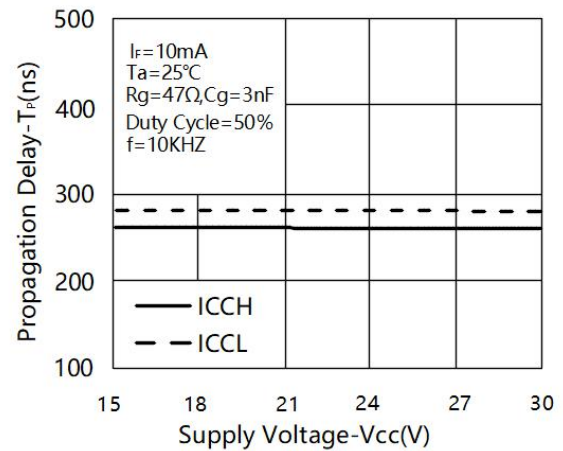


Fig.9 Propagation Delay vs Forward Current

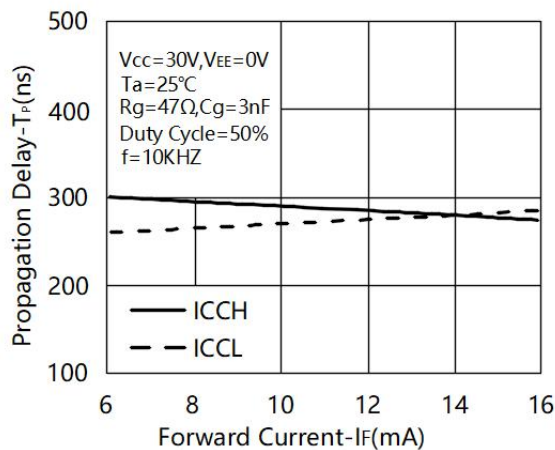


Fig.10 Propagation Delay vs Ambient Temperature

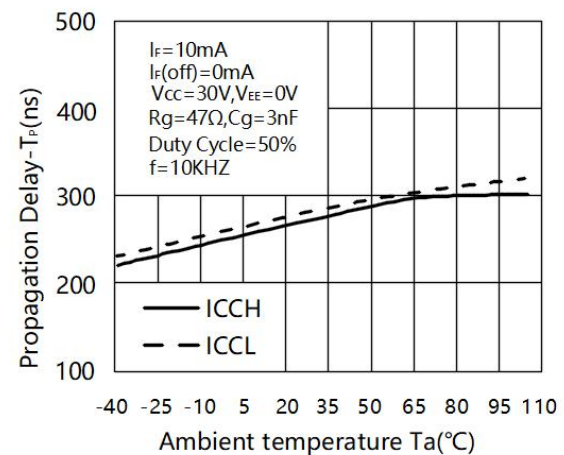
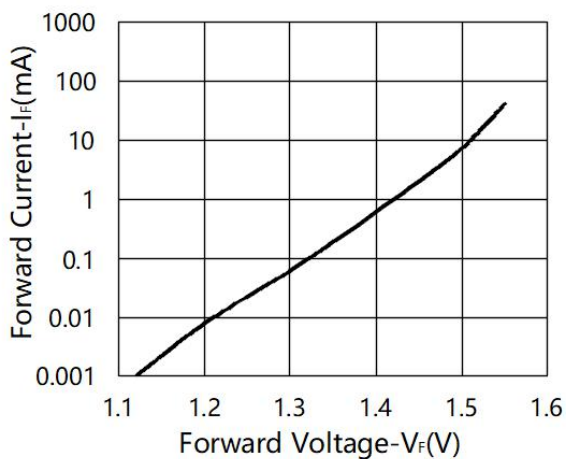


Fig.11 Forward Current vs Forward Voltage



◆ 测试电路图 Test Circuits Diagrams

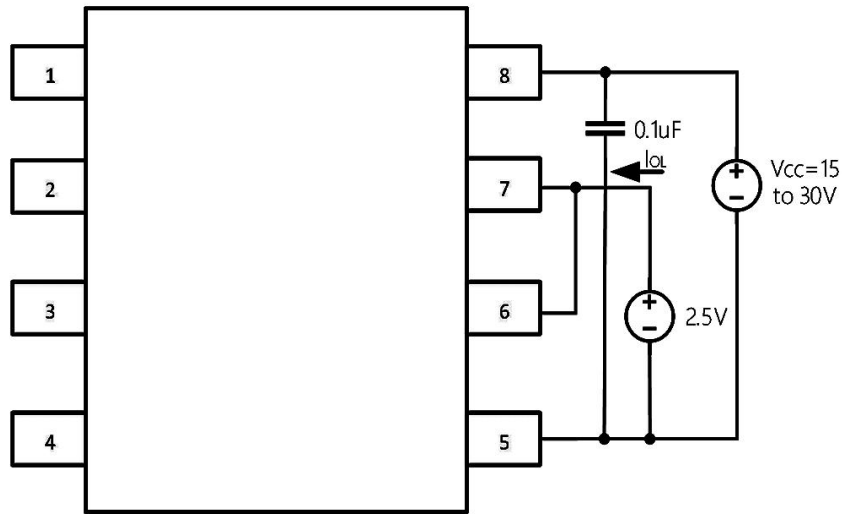


Fig.12 I_{OL} Pulsed Test Circuit

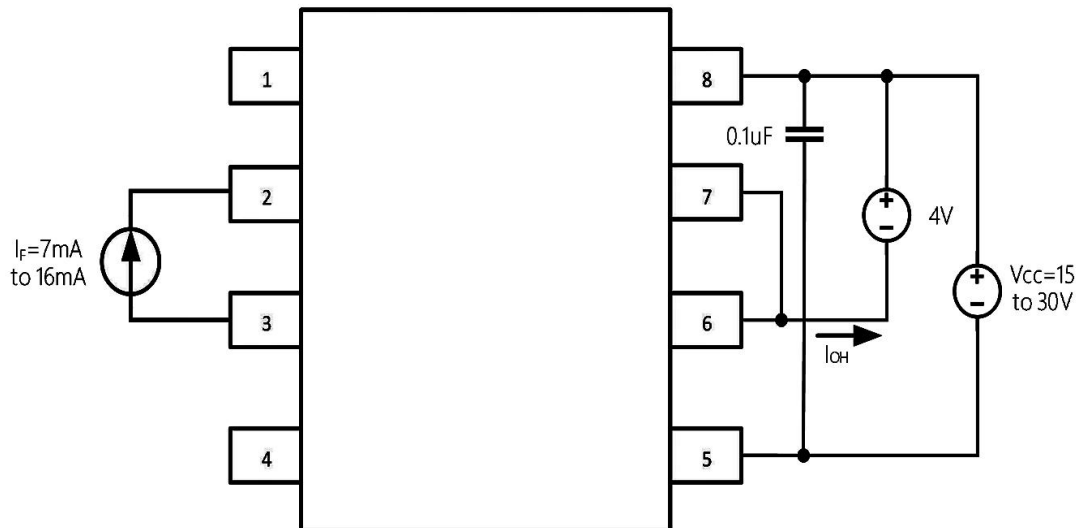


Fig.13 I_{OH} Pulsed Test Circuit

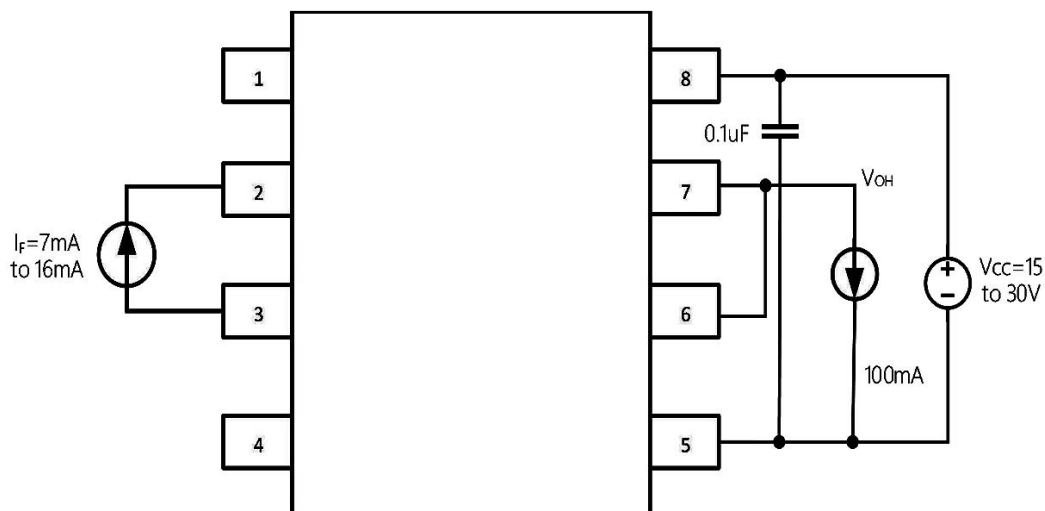


Fig.14 V_{OH} Pulsed Test Circuit

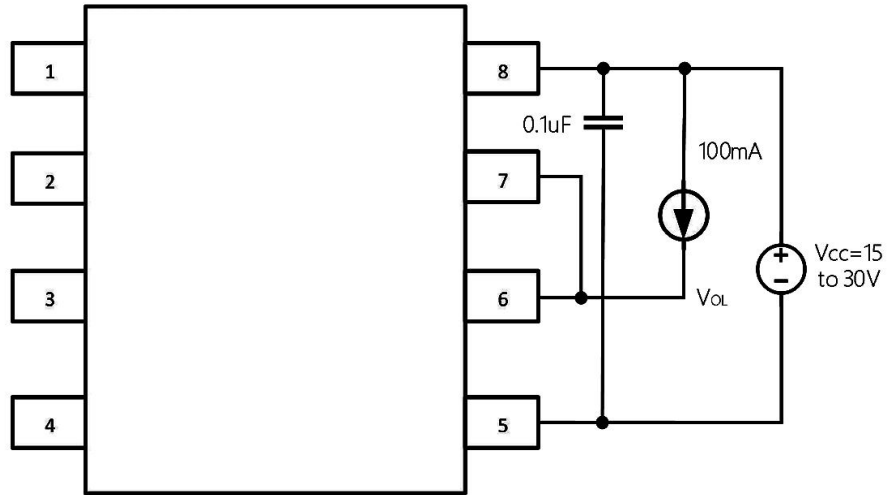


Fig.15 V_{OL} Pulsed Test Circuit

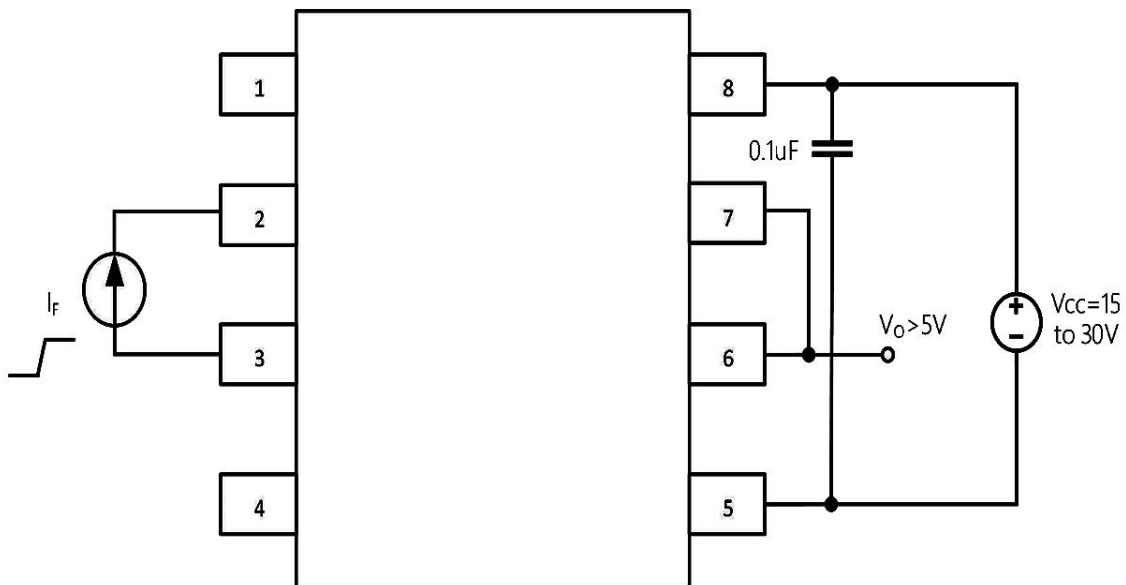


Fig.16 I_{FLH} Pulsed Test Circuit

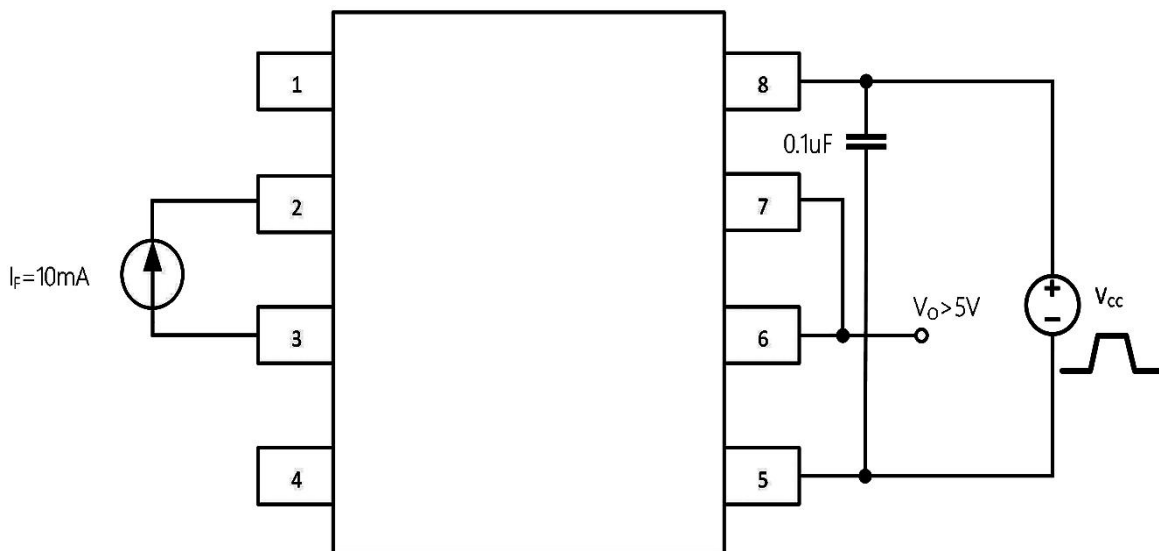


Fig.17 UVLO Test Circuit

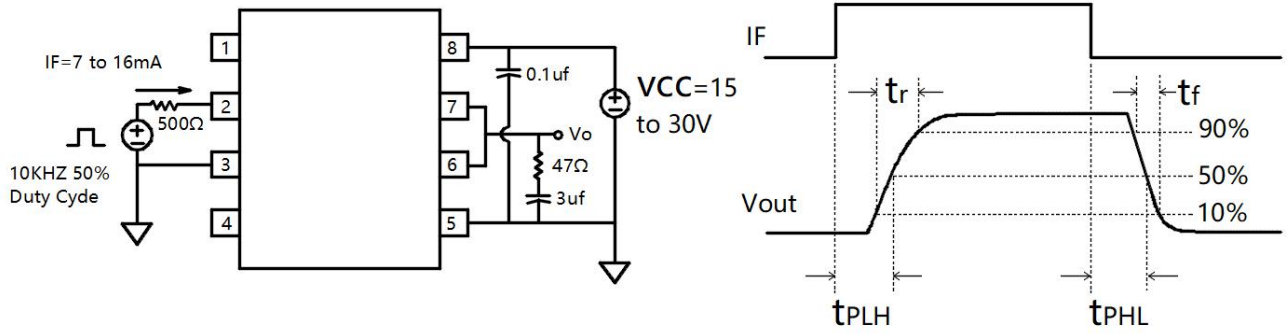


Fig.18 T_{PHL} 、 T_{PLH} 、 T_R 、 T_F Test Circuit

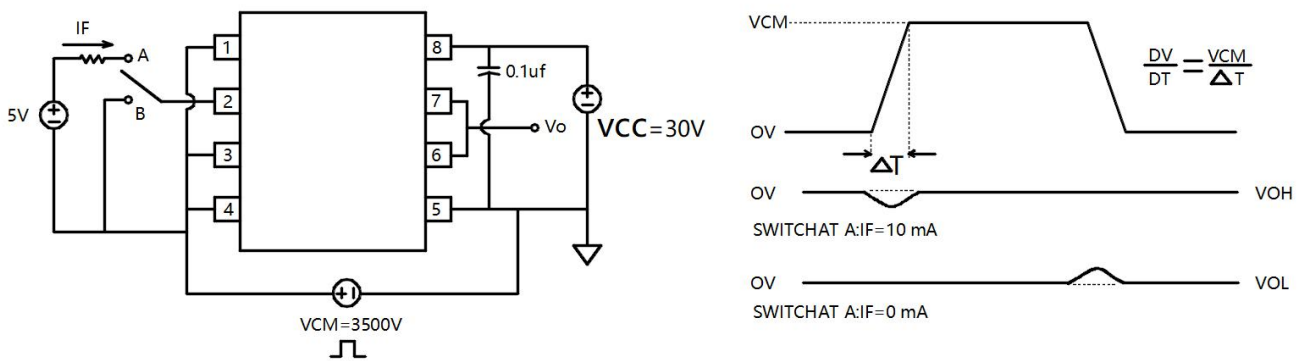
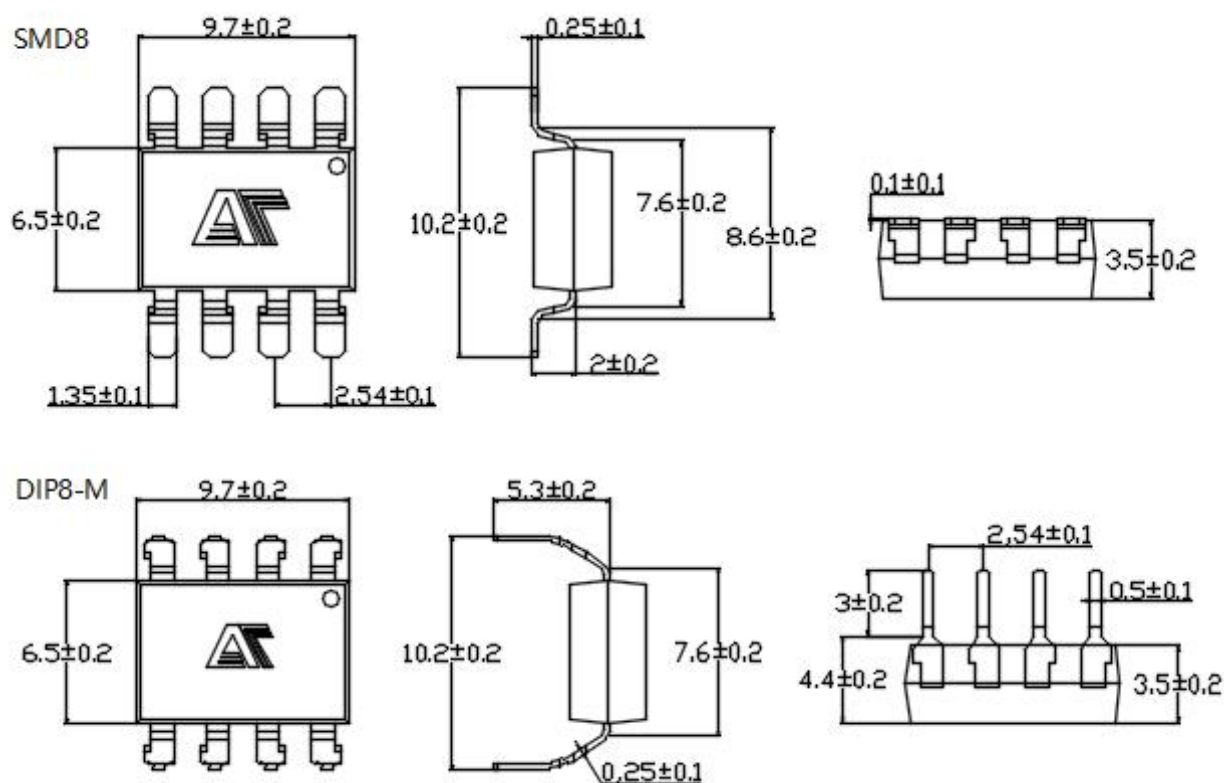


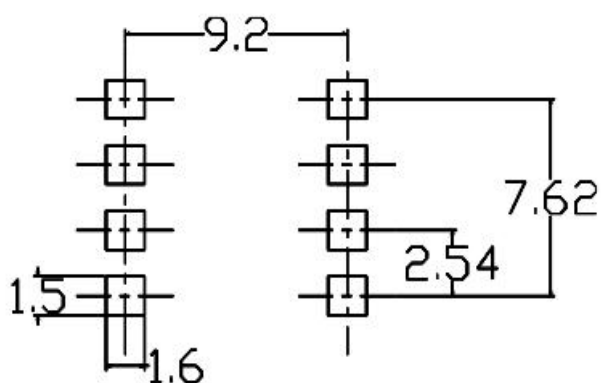
Fig.19 CMR Test Circuit

◆ 外形尺寸Overall dimension



推荐焊盘:

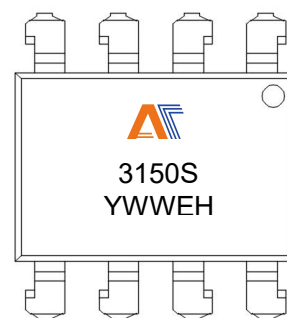
Recommended



单位: mm

◆ 印字信息 Marking Information

- 印字中 “  ” 为奥特品牌LOGO
“  ” denotes LOGO
- 印字中 “Y” 代表年份； A(2018),B(2019),C(2020)
“Y” denotes YEAR: A(2018), B(2019), C(2020)
- 印字中 “WW” 代表周号
“WW” denotes Week' s number
- 印字中 “ E” 代表内部代码
“E” denotes Internal code
- 印字中的 “H” 代表无卤
“H” denotes Halogen-free

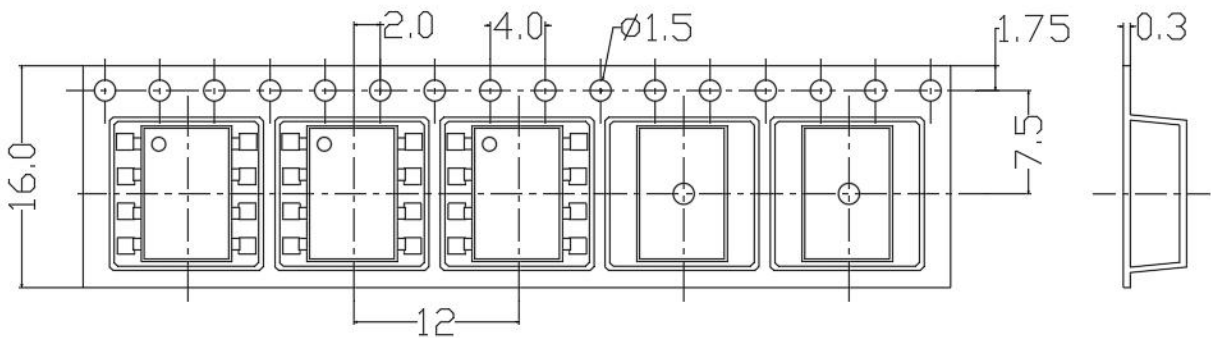
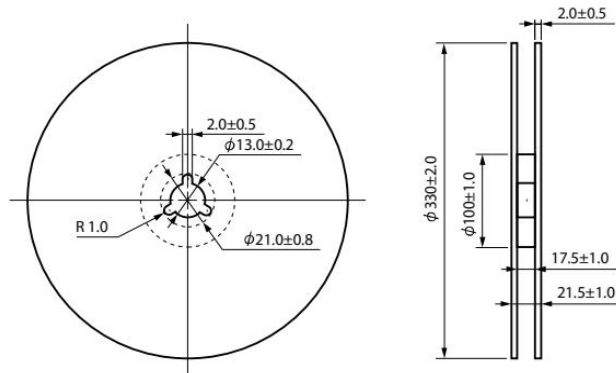


◆ 包装packing

封装形式	包装方式	盘数量	盒数量	箱数量	静电袋规格	盒规格	箱(双瓦楞)规格	备注
SMD8	卷盘 ($\phi 330$ mm蓝盘)	1000 只/盘	2 盘/盒	10 盒/箱	450*390*0.1mm	340*60*340mm	620*360*365mm	首尾端空至少200mm
DIP8	管装 (500*12*11mm)	45 只/管	50 管/盒	10 盒/箱	不适用	525*128*56mm	535*275*300mm	每管使用蓝白胶塞，方向须一致
Package Type	Packing Form	Quantity per Reel	Quantity per Box	Quantity per Carton	Antistatic Bag Specification	Box Specification	Carton Specification	Note
SMD8	Reel ($\phi 330$ mm Blue)	1000 pcs/reel	2 reels/box	10 boxes/ctn	450*390*0.1mm	340*60*340mm	620*360*365mm	Leave at least 200mm of blank space at both ends
DIP8	Tube (500*12*11mm)	45 pcs/tube	50 tubes/box	10 boxes/ctn	NA	525*128*56mm	535*275*300mm	Use blue and white rubber plugs for each tube in the same direction

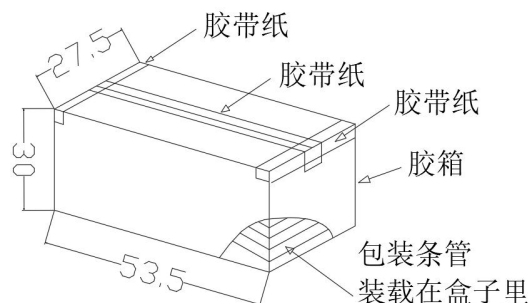
• 编带包装 Tape & Reel

- 1) 每卷数量: 2000 只;
Qty/reel: 2000 pcs;
- 2) 每箱数量: 40000 只;
Qty/ctn: 40000 pcs;
- 3) 内包装: 每盒 2 盘;
Inner packing: 2 reels/box;
- 4) 示意图 Schematic:



• 管条包装Tape&Tube

- 1) 每管数量: 45 只。
Qty/Tube : 45 pcs.
- 2) 每箱数量: 22500 只。
Qty/ctn: 22500 pcs.
- 3) 内包装: 每盒 50 管。
Inner packing: 50 Tube/box.
- 4) 示意图 Schematic

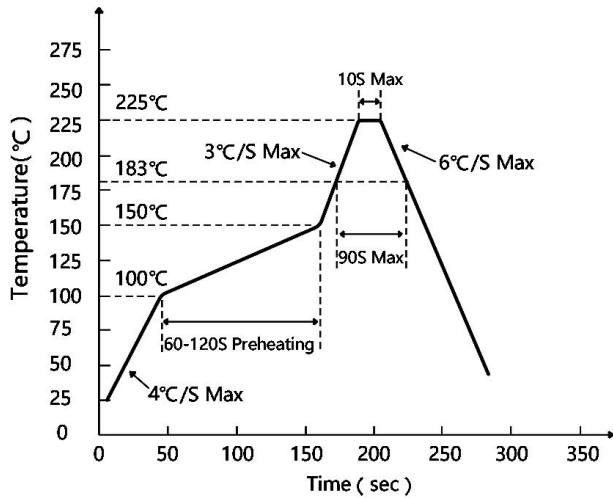


单位: mm

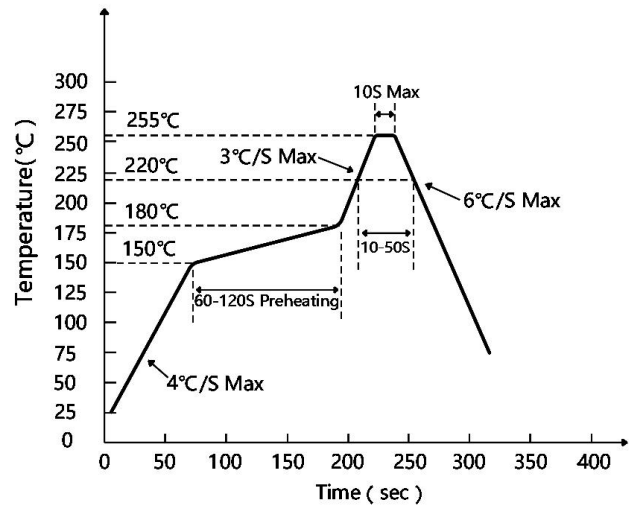
◆ 可靠性测试 Reliability Test Items And Conditions

实验项目 Test Items	参考标准 Reference	实验条件 Test Conditions	时间 Time	样品数 Quantity	判据 Criterion
可焊性 Solderability	JESD22-B102	Tsol= (245±5) °C, t=5s;	1 次1 times	22	0/22
耐焊接热 Resistance to Soldering Heat	JESD22-A106	Tsol= (260±5) °C, t=10s	3 次3 times	22	0/22
静电放电 ESD-HBM	JESD22-A114	Ta=25°C, HBM (2000V)	正反各 3 次 P&N 3 times	10	0/10
高温贮存 High emperature Storage	JESD22-A103	Ta=125°C	1000h	22	0/22
低温贮存 Low Temperature Storage	JESD22-A119	Ta= -55°C	1000h	22	0/22
冷热冲击 Thermal Shock	JESD22-A104	-55°C(15min)←→ 125°C(15min)	循环 300 次 300 cycles	22	0/22
常温寿命试验 Lifespan Test	JESD22-A108	Ta=25°C, IF=50mA , Vcc=5V	1000h	22	0/22
高温寿命试验 DC Operating Life	JESD22-A108	Ta=110°C, IF=20mA , Vcc=5V	1000h	76	0/76
高温高湿偏压 High Temperature High Humidity bias Voltage	JESD22-A101	Ta =85°C , RH=85% IF=0mA , VCE=64V	1000h	22	0/22
高温偏压 High Temperature bias Voltage	JESD22-A108	Ta =110°C , IF=0mA , VCE=80V	1000h	22	0/22
高压蒸汽试验 High pressure steam test	JESD22-A102	P=15PSIG , 121°C, 100%RH	96h	22	0/22

◆ 回流焊温度曲线图 Solder Reflow Profile

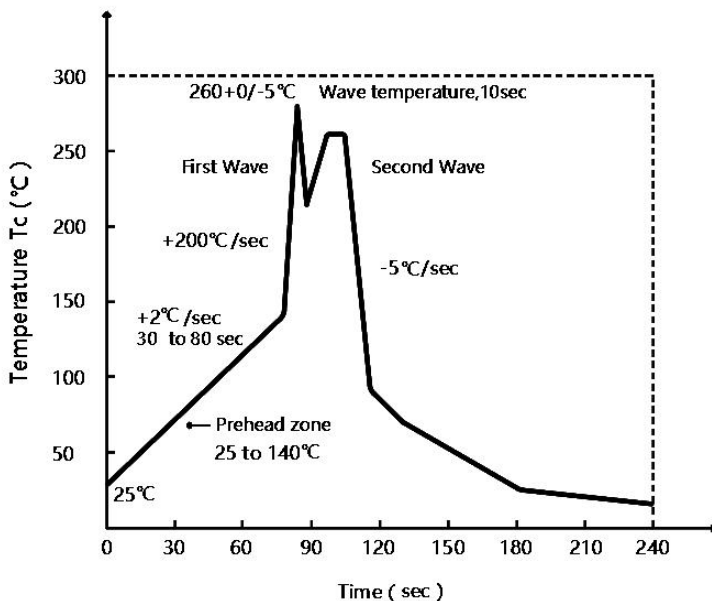


有铅制程 Lead Process



无铅制程 Lead Process

◆ 波峰焊温度曲线图 Wave Soldering Profile



◆ 手工烙铁焊接 Soldering with hand soldering iron

A. 手工烙铁焊仅用于产品返修或样品测试;

Hand soldering iron is only used for product rework or sample testing;

B. 手工烙铁焊要求: 温度 350°C ± 5°C, 时间 ≤ 3s.

Hand soldering iron requirements: Temperature: 350°C ± 5°C, within 3s.

◆ 注意 Attention

- 奥特半导体实施动态技术迭代机制，产品规格可能随工艺升级调整，最新技术参数以官网发布版本为准。

AOTE implements dynamic technical updates. Specifications are subject to change. Refer to the official website for the latest version.

- 用户需严格遵循本规格书限定的操作条件，因超范围使用（包括但不限于过载、高温、非兼容电路设计）导致的器件失效，不在质量保证范围内。

Users must strictly adhere to specified conditions. Failures caused by misuse (overload, high temperature, incompatible circuits) are excluded from warranty.

- 医疗设备、工业控制等关键场景应用前，需联系技术支持获取定制化验证方案。

Contact technical support for customized validation in critical applications (medical devices, industrial control).

- 本文档有效期至2025年12月31日，后续更新将通过官网公告推送。

This document is valid until Dec 31, 2025. Updates will be notified on the official website.

- 如需对技术参数或应用方案进行进一步确认，欢迎通过以下渠道获取官方支持：

For further clarification on technical specifications or application solutions, please contact us through official channels: